





2N4391, 2N4392, 2N4393 N-Channel JFET

Support

Features

- InterFET N0132S Geometry
- Low Noise: 1.2 nV/VHz Typical
- Fast Switching
- Low Cutoff Voltage: 2N4393 < 3.0V
- RoHS Compliant
- SMT, TH, and Bare Die Package options.

Applications

- Low On Resistance Analog Switches
- Choppers
- Commutators

Description

The -40V InterFET 2N4391, 2N4392 and 2N4393 are targeted for switch, chopper and commutator designs. Gate leakages are typically less than 50pA at room temperatures. The 2N4393 has a cutoff voltage of less than 3.0V ideal for low-level power supplies. The TO-18 package is hermetically sealed and suitable for military applications.















Product Summary

Parameters		2N4391 Min	2N4392 Min	2N4393 Min	Unit	
BV_{GSS}	Gate to Source Breakdown Voltage	-40	-40	-40	V	
I _{DSS}	Drain to Source Saturation Current	50	25	5	mA	
V _{GS(off)}	Gate to Source Cutoff Voltage	-4	-2	-0.5	V	

Ordering Information Custom Part and Binning Options Available

Part Number	Description	Case	Packaging
2N4391; 2N4392; 2N4393	Through-Hole	TO-18	Bulk
PN4391; PN4392; PN4393	Through-Hole	TO-92	Bulk
SMP4391; SMP4392;			
SMP4393	Surface Mount	SOT23	Bulk
SMP4391TR; SMP4392TR	7" Tape and Reel: Max 3,000 Pieces		Minimum 1,000 Pieces
SMP4393TR	13" Tape and Reel: Max 9,000 Pieces	SOT23	Tape and Reel
2N4391COT; 2N4392COT			
2N4393COT	Chip Orientated Tray (COT Waffle Pack)	СОТ	400/Waffle Pack
2N4391CFT; 2N4392CFT			
2N4393CFT	Chip Face-up Tray (CFT Waffle Pack)	CFT	400/Waffle Pack



Disclaimer: It is the Buyers responsibility for designing, validating and testing the end application under all field use cases and extreme use conditions. Guaranteeing the application meets required standards, regulatory compliance, and all safety and security requirements is the responsibility of the Buyer. These resources are subject to change without notice.







Electrical Characteristics

Maximum Ratings (@ T_A = 25°C, Unless otherwise specified)

	Parameters	Value	Unit	
VRGS	Reverse Gate Source and Gate Drain Voltage	-40	V	
I_{FG}	Continuous Forward Gate Current	50	mA	
PD	Continuous Device Power Dissipation	1800	mW	
Р	Power Derating	12	mW/°C	
Τı	Operating Junction Temperature	-55 to 125	°C	
T _{STG}	Storage Temperature	-65 to 150	°C	

Support

Static Characteristics (@ TA = 25°C, Unless otherwise specified)

			2N4391		2N4392		2N4393		
	Parameters	Conditions	Min	Max	Min	Max	Min	Max	Unit
V(BR)GSS	Gate to Source Breakdown Voltage	V _{DS} = 0V, I _G = -1µA	-40		-40		-40		v
I _{GSS}	Gate to Source Reverse Current	V _{DS} = -20V, V _{GS} = 0V, T _A = 25°C V _{DS} = -20V, V _{GS} = 0V, T _A = 150°C		-100 -200		-100 -200		-100 -200	pA nA
V _{GS(OFF)}	Gate to Source Cutoff Voltage	V _{DS} = 20V, I _D = 1nA	-4	-10	-2	-5	-0.5	-3	v
V _{GS(F)}	Gate to Source Forward Voltage	V _{DS} = 0V, I _G = 1mA		1		1		1	v
I _{DSS}	Drain to Source Saturation Current	$V_{GS} = 0V, V_{DS} = 20V$ (Pulsed)	50	150	25	75	5	30	mA
	Drain Cutoff Current	V _{DS} = 20V, V _{GS} = -5V, T _A = 25°C V _{DS} = 20V, V _{GS} = -5V, T _A = 150°C						100 200	pA nA
Id(off)		V _{DS} = 20V, V _{GS} = -7V, T _A = 25°C V _{DS} = 20V, V _{GS} = -7V, T _A = 150°C				100 200			pA nA
		V _{DS} = 20V, V _{GS} = -12V, T _A = 25°C V _{DS} = 20V, V _{GS} = -12V, T _A = 150°C		100 200					pA nA
.,	Drain to Source ON Voltage	$V_{GS} = 0V, I_D = 3mA$						0.4	
Vds(on)		$V_{GS} = 0V, I_D = 6mA$ $V_{GS} = 0V, I_D = 12mA$		0.4		0.4			V
Rds(on)	Static Drain to Source ON Resistance	V _{GS} = 0V, I _D = 1mA		30		60		100	Ω

Dynamic Characteristics (@ TA = 25°C, Unless otherwise specified)

			2N4391		2N4392		2N4393		
	Parameters	Conditions	Min	Max	Min	Max	Min	Max	Unit
Rds(on)	Drain to Source ON Resistance	V_{GS} = 0V, I_D = 0A, f = 1kHz		30		60		100	Ω
C _{iss}	Input Capacitance	$V_{DS} = 20V, V_{GS} = 0V, f = 1MHz$		14		14		14	рF
	Reverse Transfer Capacitance	$V_{DS} = 0V$, $V_{GS} = -5V$, $f = 1MHz$						3.5	
Crss		V _{DS} = 0V, V _{GS} = -7V, f = 1MHz				3.5			рF
		V _{DS} = 0V, V _{GS} = -12V, f = 1MHz		3.5					
t _d	Turn-On Delay Time	V_{DD} = 10V, $V_{GS(ON)}$ = 0V		15		15		15	ns
tr	Rise Time	V_{DD} = 10V, $V_{GS(ON)}$ = 0V		5		5		5	ns
t _{D(OFF)}	Turn-Off Delay Time	$V_{DD} = 10V, V_{GS(ON)} = 0V$		20		35		50	ns
t _f	Fall Time	$V_{DD} = 10V, V_{GS(ON)} = 0V$		15		20		30	ns



Technical

Support

Order

Now

SOT23 (TO-236AB) Mechanical and Layout Data

Package Outline Data





Suggested Pad Layout





- 1. All linear dimensions are in millimeters.
- 2. Package weight approximately 0.12 grams
- 3. Molded plastic case UL 94V-0 rated
- For Tape and Reel specifications refer to InterFET CTC-021 Tape and Reel Specification, Document number: IF39002
- 5. Bulk product is shipped in standard ESD shipping material
- 6. Refer to JEDEC standards for additional information.

- 1. All linear dimensions are in millimeters.
- 2. The suggested land pattern dimensions have been provided for reference only. A more robust pattern may be desired for wave soldering.





Order

Now

TO-18 Mechanical and Layout Data

Package Outline Data



Suggested Through-Hole Layout



- 1. All linear dimensions are in millimeters.
- 2. Package weight approximately 0.29 grams
- 3. Bulk product is shipped in standard ESD shipping material
- 4. Refer to JEDEC standards for additional information.

- 1. All linear dimensions are in millimeters.
- 2. The suggested land pattern dimensions have been provided as a straight lead reference only. A more robust pattern may be desired for wave soldering and/or bent lead configurations.



Technical Order Now

Support

TO-92 Mechanical and Layout Data

Package Outline Data





Suggested Through-Hole Layout





- All linear dimensions are in millimeters. 1.
- 2. Package weight approximately 0.19 grams
- 3. Molded plastic case UL 94V-0 rated
- 4. Bulk product is shipped in standard ESD shipping material
- 5. Refer to JEDEC standards for additional information.

- 1. All linear dimensions are in millimeters.
- 2. The suggested land pattern dimensions have been provided as a straight lead reference only. A more robust pattern may be desired for wave soldering and/or bent lead configurations.